

IRFR3412TRLPBF

IRFR3412TRLPBF Information



For Reference Only

Part Number IRFR3412TRLPBF
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 48A DPAK

Package TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRFR3412TRLPBF Specifications

Manufacturer Part Number IRFR3412TRLPBF Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 48A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 89nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3430pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 140W (Tc) Rds On (Max) @ Id, Vgs 25 mOhm @ 29A, 10V Operating Temperature -55°C ~ 175°C (TI) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 Report errors?		
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SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C48A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5.5V @ 250μAGate Charge (Qg) (Max) @ Vgs89nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3430pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs25 mOhm @ 29A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63		Transistors - FETs, MOSFETs - Single
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C48A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5.5V @ 250μAGate Charge (Qg) (Max) @ Vgs89nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3430pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs25 mOhm @ 29A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	HEXFET?
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Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 89nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 140W (Tc) Rds On (Max) @ Id, Vgs 25 mOhm @ 29A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 5.5V @ 250μA 89nC @ 10V 140W 150D 160D 160D	Current - Continuous Drain (Id) @ 25°C	48A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Journal Type Surface Mount Supplier Device Package Package / Case 89nC @ 10V 3430pF @ 25V 140W TC) Surface Mount Supplier Device Package D-Pak TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 25 mOhm @ 29A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	5.5V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs25 mOhm @ 29A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	89nC @ 10V
FET Feature - 140W (Tc) Rds On (Max) @ Id, Vgs	Input Capacitance (Ciss) (Max) @ Vds	3430pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 25 mOhm @ 29A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs25 mOhm @ 29A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	140W (Tc)
Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	25 mOhm @ 29A, 10V
Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	D-Pak
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

IRFR3412TRLPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFR3412TRLPBF Payment Methods



















IRFR3412TRLPBF Shipping Methods













If you have any question about IRFR3412TRLPBF, please do not hesitate to contact us!

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